

ABSTRACT OF THE DISCLOSURE

A thin film transistor includes a substrate having an upper side; a plurality of parallel-connected active layers supported on the upper side of the substrate; spaces defined between the substrate and the active layers; a first insulating layer on the plurality of active layers; a
5 gate electrode on the first insulating layer over the plurality of active layers; and source and drain electrodes contacting the plurality of the active layers. The active layers of the thin film transistor are laser annealed to polycrystalline silicon. The spaces result in large polysilicon grains that result in good electrical characteristics.